

# SANYO Semiconductors DATA SHEET

N-Channel Silicon MOSFET

# **FW274** — General-Purpose Switching Device Applications

#### **Features**

- · 4V drive.
- · Composite type, facilitating high-density mounting.

#### **Specifications**

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V <sub>DSS</sub>		30	V
Gate-to-Source Voltage	VGSS		±20	V
Drain Current (DC)	ID		6	Α
Drain Current (PW≤10s)	ID	Duty cycle≤1%	6.5	Α
Drain Current (PW≤10μs)	IDP	Duty cycle≤1%	24	Α
Allowable Power Dissipation	PD	When mounted on ceramic substrate (2000mm²x0.8mm) 1unit, PW≤10s	1.8	W
Total Dissipation	PT	When mounted on ceramic substrate (2000mm²×0.8mm), PW≤10s	2.2	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

#### Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Unit
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0V	30			V
Zero-Gate Voltage Drain Current	IDSS	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V			1	μΑ
Gate-to-Source Leakage Current	IGSS	V <sub>GS</sub> =±16V, V <sub>DS</sub> =0V			±10	μΑ
Cutoff Voltage	VGS(off)	VDS=10V, ID=1mA	1.2		2.6	V
Forward Transfer Admittance	yfs	V <sub>DS</sub> =10V, I <sub>D</sub> =6A	1.8	3		S
Static Drain-to-Source On-State Resistance	R <sub>DS</sub> (on)1	I <sub>D</sub> =6A, V <sub>G</sub> S=10V		28	37	$m\Omega$
	R <sub>DS</sub> (on)2	I <sub>D</sub> =3A, V <sub>G</sub> S=4.5V		43	61	mΩ
	RDS(on)3	ID=3A, VGS=4V		52	73	mΩ

Marking: W274 Continued on next page.

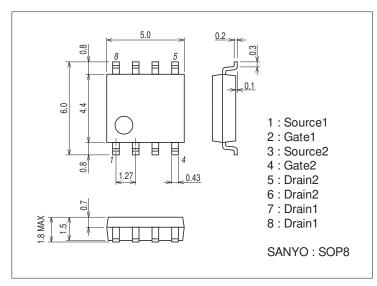
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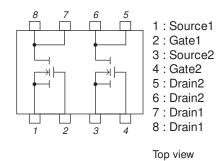
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Unit
Input Capacitance	Ciss	V <sub>DS</sub> =10V, f=1MHz		490		pF
Output Capacitance	Coss	V <sub>DS</sub> =10V, f=1MHz		85		pF
Reverse Transfer Capacitance	Crss	V <sub>DS</sub> =10V, f=1MHz		45		pF
Turn-ON Delay Time	t <sub>d</sub> (on)	See specified Test Circuit.		8		ns
Rise Time	t <sub>r</sub>	See specified Test Circuit.		45		ns
Turn-OFF Delay Time	t <sub>d</sub> (off)	See specified Test Circuit.		31		ns
Fall Time	tf	See specified Test Circuit.		28		ns
Total Gate Charge	Qg	V <sub>DS</sub> =15V, V <sub>GS</sub> =10V, I <sub>D</sub> =6A		9.1		nC
Gate-to-Source Charge	Qgs	V <sub>DS</sub> =15V, V <sub>GS</sub> =10V, I <sub>D</sub> =6A		1.7		nC
Gate-to-Drain "Miller" Charge	Qgd	V <sub>DS</sub> =15V, V <sub>GS</sub> =10V, I <sub>D</sub> =6A		1.7		nC
Diode Forward Voltage	V <sub>SD</sub>	IS=6A, VGS=0V		0.84	1.2	V

## **Package Dimensions**

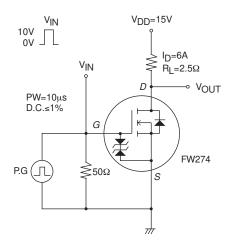
unit : mm (typ) 7005A-003

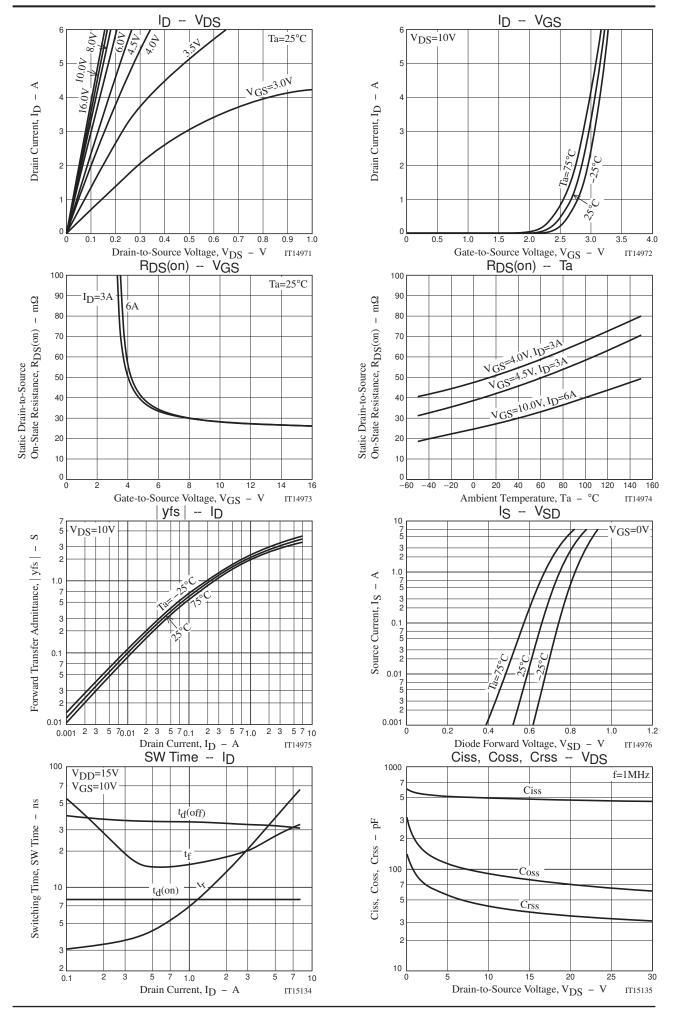


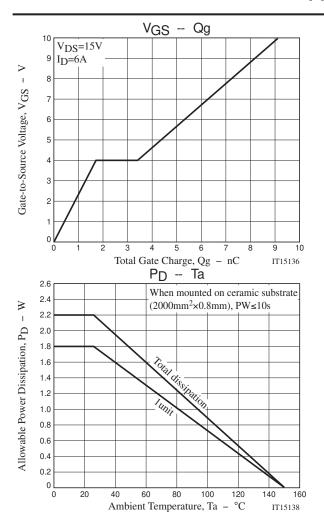
#### **Electrical Connection**

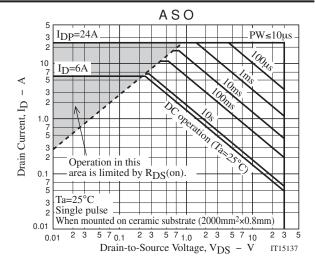


## **Switching Time Test Circuit**









Note on usage: Since the FW274 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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